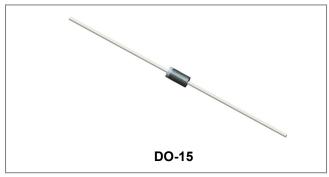






### SF21G-SF28G SUPER FAST RECTIFIER



#### **Features**

- · Super fast switching for high efficiency
- Low leakage current
- High forward surge capability
- Solder dip 260 ° C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



#### **Mechanical Data**

- Case: JEDEC DO-15 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.014 ounce, 0.40 grams

## Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	SF21G	SF22G	SF23G	SF24G	SF25G	SF26G	SF28G	Units
Maximum repetitive peak reverse voltage	$V_{RRM}$	50	100	150	200	300	400	600	V
Maximum RMS voltage	V <sub>RMS</sub>	35	70	105	140	210	280	420	V
Maximum DC blocking voltage	V <sub>DC</sub>	50	100	150	200	300	400	600	V
Maximum average forward rectified current 0.375"(9.5mm) lead length at $T_A$ =55°C	I <sub>(AV)</sub>	2.0				Α			
Peak forward surge current 8.3ms single half sinewave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	75			Α				
Maximum instantaneous forward voltage at 2.0A	V <sub>F</sub>	0.95			1.2	5	1.7	V	
Maximum DC reverse current $T_A$ =25 $^{\circ}$ C at rated DC blocking voltage $T_A$ =100 $^{\circ}$ C	I <sub>R</sub>	5.0 50.0				μA			
Maximum Reverse Recovery Time (Note 1)	Trr	35			ns				
Typical Junction Capacitance (Note 2)	Сл	60.0 30.0			pF				
Typical Thermal Resistance (Note 3)	R <sub>0JA</sub>	50.0			°C/W				
Junction Temperature	TJ	-65 to +175			°C				
Storage Temperature Range	T <sub>STG</sub>	-65 to +175			°C				

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A. Irr=0.25A

- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 3. Thermal resistance from junction to ambient at 0.375"(9.5mm) lead length, P.C.B mounted.
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    - http://www.smc-diodes.com
       sales@ smc-diodes.com







## **Ratings and Characteristics Curves**

FIG. 1- FORWARD CURRENT DERATING CURVE

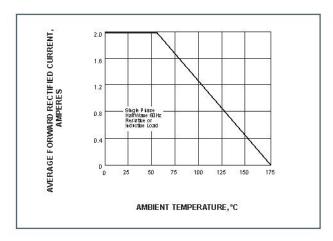


FIG. 2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

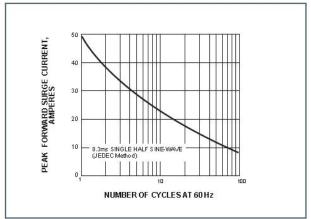


FIG. 3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

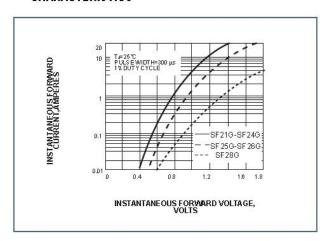


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

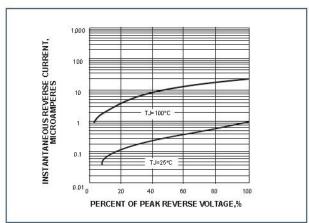
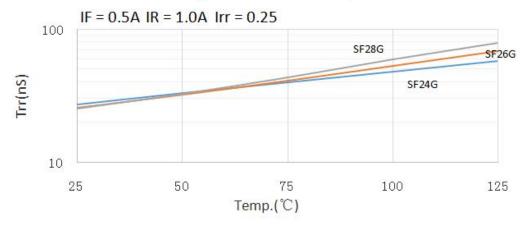


Fig.5 Trr & Temp.



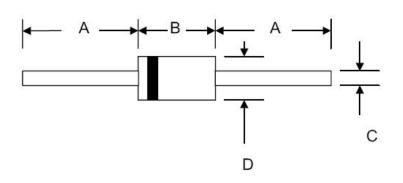
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#### **Mechanical Dimensions DO-15**



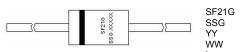
CVMDOI	Millim	neters	Inches			
SYMBOL	Min.	Max.	Min.	Max.		
А	25.4	-	1.000	-		
В	5.5	7.62	0.217	0.300		
С	0.7	0.9	0.028	0.034		
D	2.6	3.6	0.104	0.140		

## **Ordering Information**

Device Package		Shipping		
SF21G				
THRU	DO-15 (Pb-Free)	3000pcs /tape		
SF28G	, , ,			

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**



Where XXXXX is YYWWL

 SF21G
 = Part Name

 SSG
 = SSG

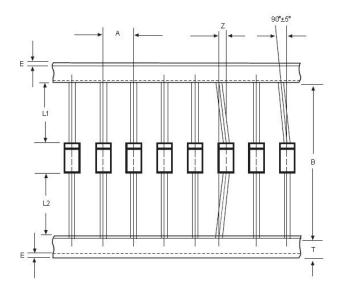
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

**Cautions:** Molding resin Epoxy resin UL:94V-0

## **Carrier Tape Specification DO-15**



SYMBOL	Millimeters			
STWIBOL	Min.	Max.		
А	4.50	5.50		
В	50.9	53.9		
Z	-	1.20		
Т	5.60	6.40		
Е	-	0.80		
IL1-L2I	-	1.0		

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